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H05B 33/10

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(43)

10-2004-0097918
2004 11 18

(21)10-2004-0033019
(22)2004 05 11

(30)JP-P-2003-00132791 2003 05 12(JP)

(71)가 가가가 6 7 35

(72), , 가 - , 가 6- ,7-35 가 가

(74)

:

(54), ,

(aperture ratio)

(continuous organic layer)

(organic light emitting device)

(m

atrix configuration) 2

(dissolved) , 가

(notch part)

(contact part) , 2

(voltage drop)가

19

- 1 .
- 2 1 .
- 3 2 .
- 4 3 .

5	4		.
6	5		.
7	6		.
8			.
9		(outline)	.
10	9		.
11	10		.
12	11	-	.
13	11	12	.
14	13	-	.
15	13	14	.
16	15	-	.
17	15	16	.
18	17		.
19	17	18	.
20	18		.
21	18		.
22	17	19	.
23	17	19	.
24	23		.
25	24	-	.
26	24	-	.
27	24		.
28	27	XX-XX	.
29	27	XX -XX	.
30	27		.
31a	31b	30	.
32	31a	31b	.

33 32

34 33

35 18

< >

10R, 10G, 10B : 11 :

12 : TFT 12A, 15 :

12B : 13 :

13A : 14 : 1

15A : 16 : 2

16A : 16B :

16C : 17A : ()

17R, 17G, 17B : 18 :

21 : 22R, 22G, 22B :

30 : 40 :

40A : 41 :

41A, 41C : 50 :

51 : 52 :

54 : 55 :

, , (dispaly unit) ,
 , (organic light emitting device) ,
 ,
 . ,
 (liquid crystal display) , (organic lig
 ht emitting device) 가 , 가
 (self-luminous type display) , (viewing angle) ,
 (high-definition high-speed) 가
 .

1 7 . , 1 , 1

(114) (111) 1 (114) (patterned)
(planarizing layer)
TFT(Thin Film Transistor :)

15) 1 2 (114) (115) 1 (114) (1)
(opening)(115A)가

3 (116A) (116A) (115) (116B) (111)
(peripheral area) (bus line) (trunk-shaped) (power source)() (li
ght emitting parts) (wiring resistance) (emission unevenness)(
ge drop) (116C) 2 (116) (116B) (extraction electrode)

(110G) (117) 4
(deposition mask)(140) 5

0) 6 (110R) (117) (14)
(117) (140) 5 (110B)

7 (116) (116A) 2 (116) (111) 2
(116) (116A) (contact part)(118)

(spacer) (rib)가
가 (

2001-195008).

0) (140) (141) 가 8 (4). (14)
(evaporation source)(152)
140) (117) (140) (141) (152) (plate) (

(117) (152) (color unevenness)
(effective light emitting region)(117A) (117)
가 (140) (117A)

(aperture ratio)가

1 (aperture ratio) (d
eposition mask) , (display unit)

2 가

mn) (matrix configuration) (line) (colu
(continuous organic layer)

2 (stripe-shaped ope
ning) (body part) , (prot
rusion)

; 1 1 ; 1 1
 2 ; (notch part) 1
 ; (cover) 2 2
 1 ; 1 ;
 1 1 ; 1
 1 (side wall part) 2 (notch part)
 ; (contact part) 2
 2 (body part)
 (stripe-shaped opening) 가, (opening) (extensional direction)
 2 (contact part) (protrusion)가
 (notch part)
 1 1
 1 2
 2 1
 2 (element)
 2 가, 1
 2 (wiring resistance) 가
 가
 []
 가
 9 31b ,
 nic light emitting device) 9 (pixel) , (11) (ultrathin organic light emitting device)
 (10R, 10G, 10B) (10G) , (10B) 3
 (10R) , (three primary color device)
 (10R, 10G, 10B)가 10 , TFT
 (11) , PSG(Phosphor Silicon Nitride)
 (12A) (Al) (Al)-
 (12B) TFT(12) ()
 () (12A) (contact hole)

e type) (12B) . TFT(12) (bottom gat
 (top gate type) .
 layer)(13) 10 (polyimide) (planarizing
 (exposure) (spin coat method) (11) (13)
 (13) TFT(12)가 (11) (patterned) (13A)
 (10R, 10G, 10B) ()
 (13) (13A) (SiO₂) (inorganic material)
 (13)
 (lithography) 11 12 , 1 () (14) (sputtering)
) (13A) (12B) . 1 (14) 1 (14)
 1 (14) 200nm 가 (Pt), (Au), (Ag), (Cr), (W)
 (work function) (simple substance)
 , 13 14 , (15) CVD(Chemical Vapor Deposition :
) , 1 (14) (15A)
 (15) , 2 (16) 1 (14)
 (10R, 10G, 10B) 가
 (15) 600nm
 , 15 16 , (16A)
 (15) (16A) ()
 (voltage drop) (emission unevenness){
 (central part) (peripheral part) }
 (16A) (Al) (Cr) (conductive ma
 terial) 가, 15 16 (16A)
 (bus line) (trunk-shaped) (16B) ,
 (11) (peripheral area) (16B) (11)
 (16A) (16B) (16A) (16B) (11)
 (16B) (16A) , (16A) 가 (16B)
 (16A) (16B) 가 (16B)
 (11) (16B) 가 (16A) (16B)
 (contact hole) (13)
 (extraction electrode)(16C) , 2 (16) ()
 (16B) (16C) , (Ti), (Al)
 , 17 18 , (10G) (17G)
 (41) (40) 19 ,
 (10G) (semioval notch)(17A) (17G)
 (17G) , (electron hole transport layer) (light emitting
 layer) 1 (14) (side) 가
 (electron hole injection efficiency) 가
 (electric field) 가 (17G)
 (component material) alpha -NPD (17G)
 , 1 % (Coumarin) 6 (C6) Alq₃
 17 18 (40) (Ni) (magnetic characte
 ristics) (flat plate-shaped body part)(40A) ,
 2) (41) (41) , (10R, 10G,

10B) , 가 (10G) (17G) , 17 (10G)가 18 (41) s organic layer)(17G) , (3) , (continuou (10G) (17G) (aperture ratio)가 가 (10G) (41) (protrusion)(41A) (41 A) , (17A) (pair) (41A) , (41) (17G) , (10G) (41A) (2) (41A) (15) (15A) (block) (18) (41A) (16A) 2 (16) 18 () (non-circular shape) 20 (41A) 21 (40) (18) : (41) , d1 40nm , (41) () , d 2 30nm (41) (41A) , (etching or electroforming metho d) 22 (40) (17G) (50) (vacuum chamber)(51) (17G) 3) (vent)가 (52) (51) (52) (53) (40)가 (11) (work)(5 (carry-in entrance) (52) (point source) (line source) (52) (52) , EB(Electron Beam) (17G) (53) (52) 가 (52) (mask holder)(54) (11) (40) (11) (52) (sheet magnet)(55) (17G) (17A) 가 (10R)가 (17R) 23 (10G) (17R) (17G) (17A) , (17G) (17A) (16A) (17R) 1 (14) 가 (17R) , bis[(N-naphthyl)-N-phenyl] benzidine (alpha -NPD) (17R) , 2,5-bis[4-[N-(4-methoxy phe nyl)-N-phenyl amino]] styryl benzene-1,4-dicarbonitrile (BSB) (17R) , 8-quinolinol aluminum complex (Alq₃)가 (17B) (40)가 (17A) 가 (10B) (17B) 24, 25, 26 (10G) (17G) (17B) (17A) 가, (17G) (17A) (17A) (17B) (16A) (17A) (16A)

(17B) , , 1 (14)
 , (17B) , alpha -NPD가
 (17B) , 4,4'-bis(2,2'-diphenyl vinyl) bi
 phenyl (DPVBi)가 , Alq₃
 가 .

27, 28, 29 (17R), (17G), ((17B) , (11) (cover) 2 (16) , (16) , (e)
 xtracted). 2 (16) 10nm 가 , (Ag), (Al), (Mg), ((Ca), (Na) , 2 (16) (Mg) , 2 (16)
 (Mg) (Ag) (MgAg) .

(11) 2 (16) (16A) 2 (16) (16A) 2 (16) 가,
 (18) 2 (16) (17A) , (16A) 2 (16) (16B) .
 (16B) (10R, 10G, 10B) .

30 (19) , CVD ,
 2 (16) (19) 500nm 10,000nm 가 ((SiO₂) (SiN) .

31a (10R, 10G, 10B)
 (sealing substrate)(21) (spin coat) (22R)
 (photolithography) (patterning) (firing)
 (22R)가 , 31b (22B) (22G) (22R)
 (22) , (10R, 10G, 10B) (color filter)(22) (21)
 (10R, 10G, 10B) (contrast) .

32 (thermosetting resin) (30) ((11) (10R, 10G, 10B)가 (slit nozzle type dispenser), (roll coating), (screen printing)
 (30) , 33 (11) (21)
 (22)가 (21) (11)
 (30) 가 (21)
 (22) (11) (10R, 10G, 10B) 가 (30)

1 (14) 2 (16) 가 , (21)
 (17) 가 , 가 (17R) (19 3) ((10R) , (17G) (10G) ,
 (17B) (10B) , (17R)
 가 .

가, (17R), (17G), (17B) (non-light emitt
 ing region)(,) (17A) ,
 2 (16) (16A) (18) (aperture ratio) .

34 (16C) 2 (16)
 (thin film common electrode) , (16C) (16C) 가 가
 (R1) , (R2, R3) , (16C)
 (voltage drop)가 , (central part) (peri
 pheral part) (luminance)가 . 2 (16) ,

(18)
(16C) (R1 (16A) (16C) 가 가 (R4) (thick film) 가 (R5, (16A) (18) (16C) 가 (16C) 가 (16A) (18) 가 . , (10R, 10G, 10B) (17R), (17G), (17B) (17R) (17G), (17B) (dissolved), (a perture ratio)가 가, 2 (16) (16A) (18) (17A) (18C) . ,

35 (18) (41A)가 (41) (17A) (41) (41C)가 (41) (17A) (41) (17R), (17G), (17B) (41C)가 (41) (41) (41)

0B) 2 (10R, 10G, 10B)가 (17R), (17G), (17B)가 (10R, 10G, 10B)가 (staggered shape)

(16A) (15) 1 (14)
가 , (16A) 1 (14)
1 (14)

, ,
, , (17R), (17G),
(17B)

, (21) , 1 (14), (17), 2 (16) (11)
 가 (11)
 , TFT(12) (10R, 10G, 10B) (11)
 , (10R, 10G, 10B) TFT(12) , TFT(12)가
 (aperture ratio)가 가 (21)

, 1 (14) (anode) 2 (16) (cathode)
 가 , 가 가 , 1 (14) 2 (16)
 2 (16) 가, 1 (14) 2 (16)
 (11) 가 .
 , (10R, 10G, 10B) 가 .
 가 , (10R, 10G, 10B)
 (17R), (17G), (17B)

가 (mono-color display) (color display) .

가

2

(dissolved)

가,

2 ()

가

2

가

가

(57)

1. (organic light emitting device) (line) (column) (matrix configuration) 가 (display unit) (continuous organic layer) ,

2 (stripe-shaped opening) 가 (body part) , (protrusion)

3. $\frac{1}{2}$ (semicircle), $\frac{1}{4}$ (semiellipse), $\frac{1}{n}$ (polygon)

4. 1. (pair)

6. _____, _____ (etching or electroforming) _____.

7. (magnetic characteristics)

8. (display unit), 1, 1, 1, 1, 1, 2, (notch part), (contact part), (covering), 2, 2.

9. 8 (stripe-shaped openings) (body part) (protrusion), .

10. 8, , , , , .

11. 8 (peripheral area) (bus line) (trunk-shaped), .

12. , 1, 1, 1, 1, 1, 2 (side wall part), 2, .

13. 12, , .

14.

12

15.

12

16.

12

extract)

2

(

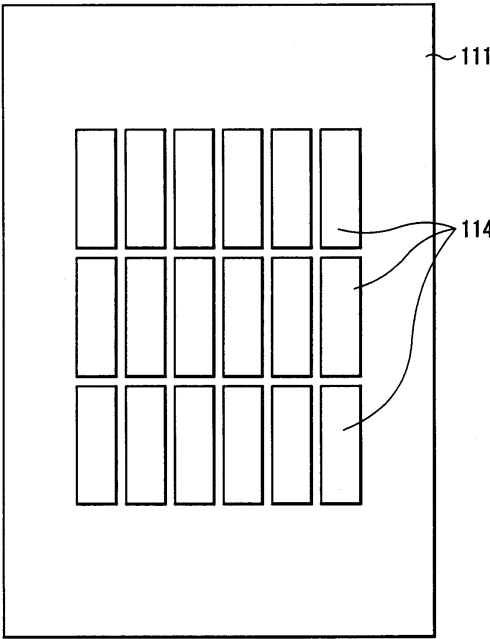
17.

12

trate)

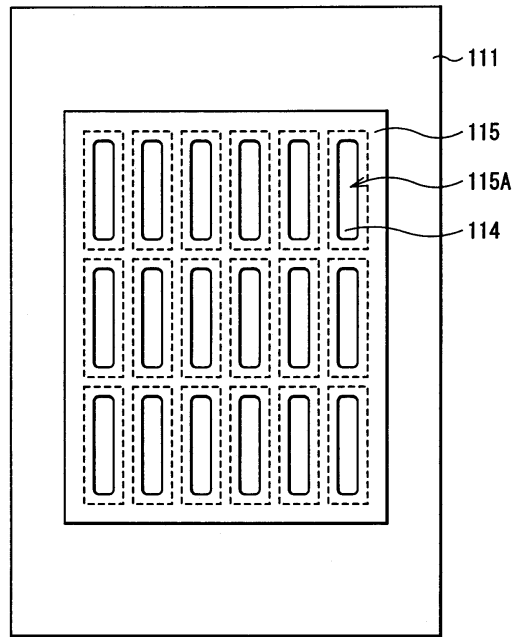
(sealing subs

1



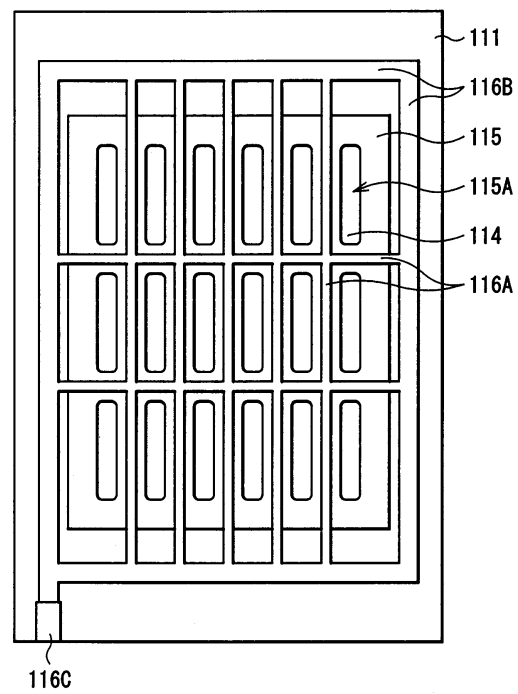
종래기술

2



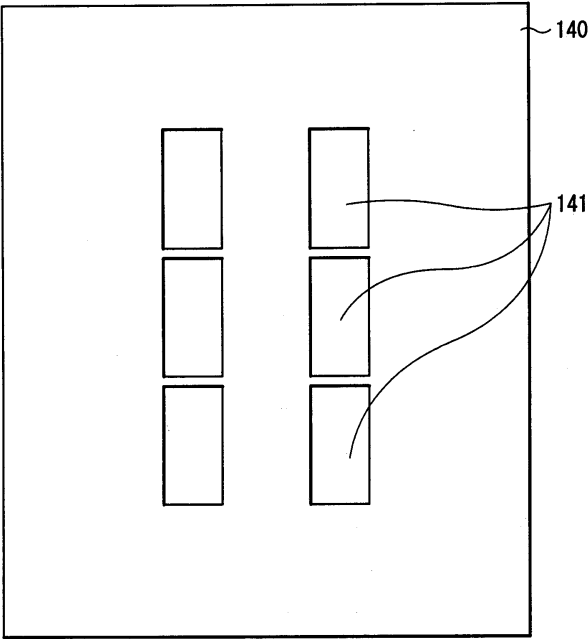
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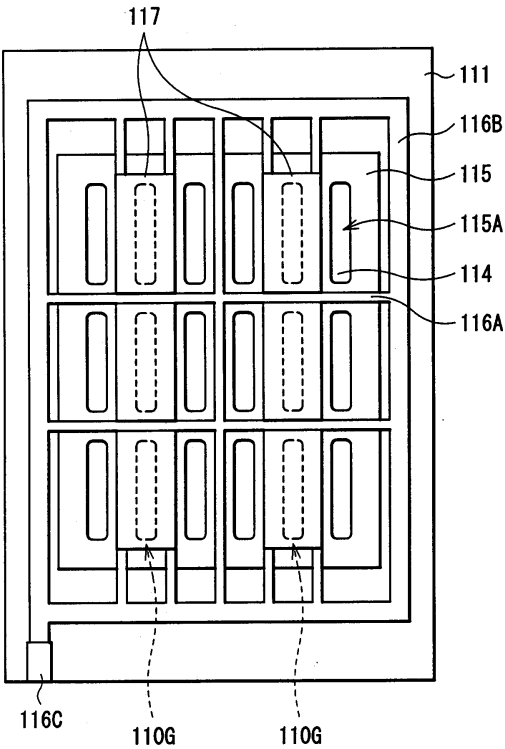
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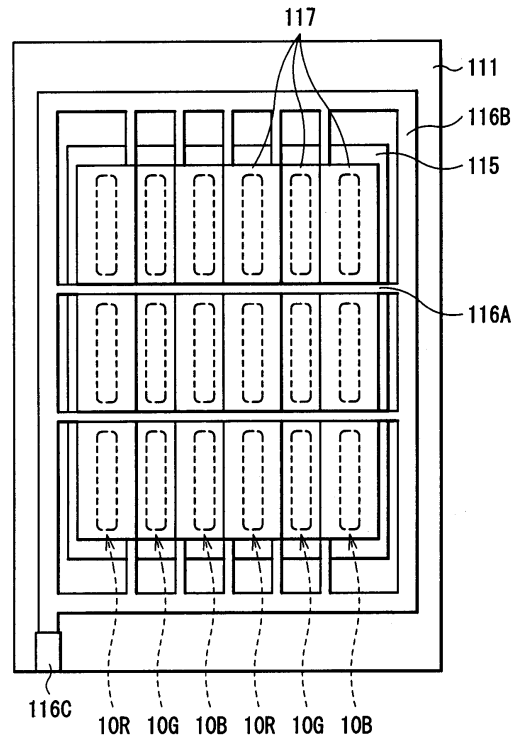
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5



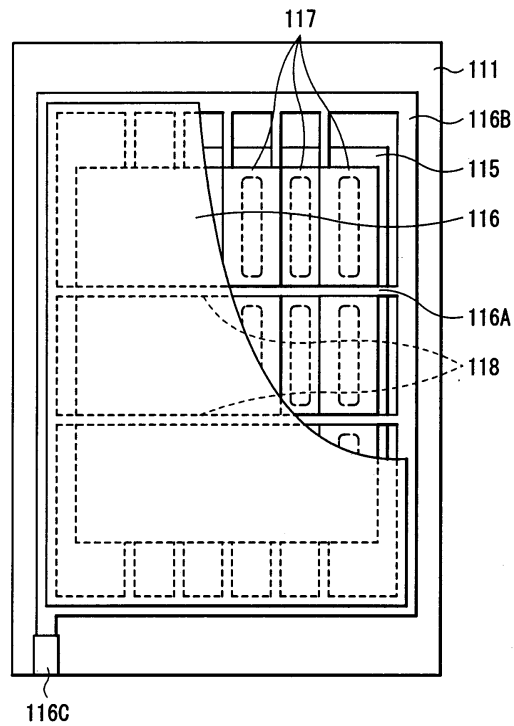
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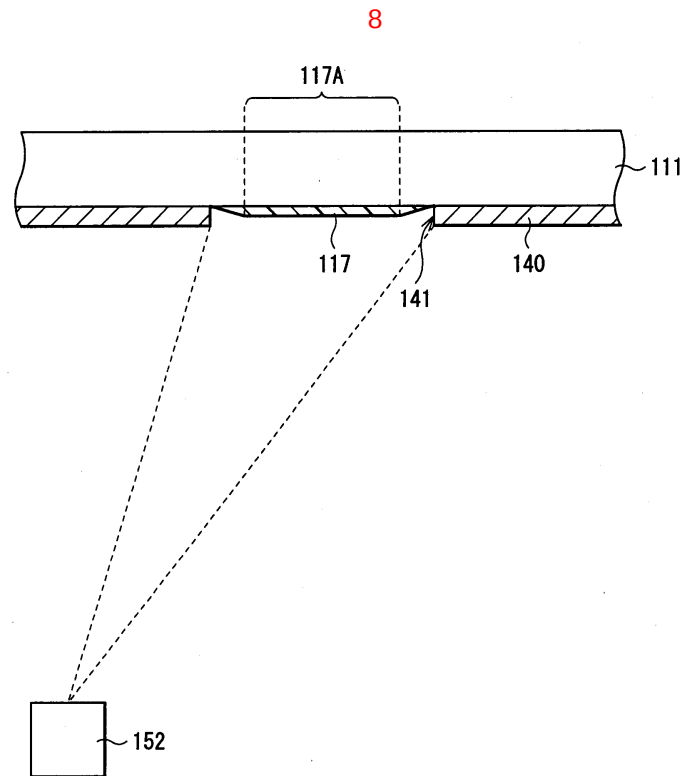


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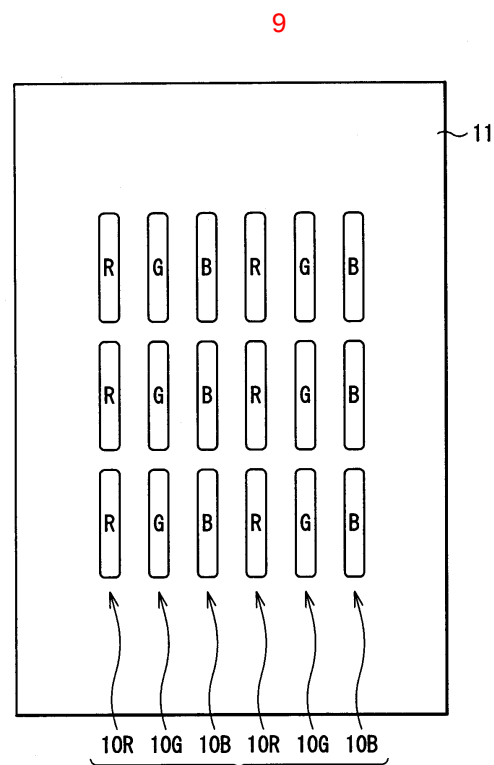
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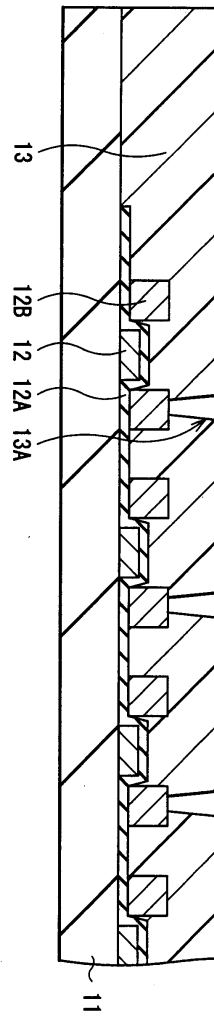


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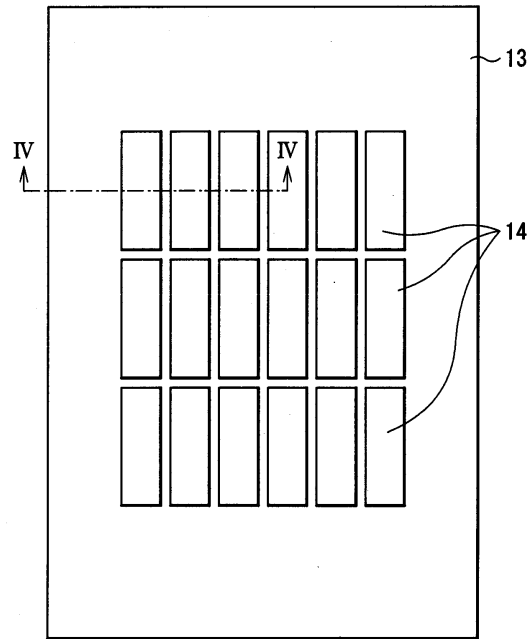


유기 발광 디바이스

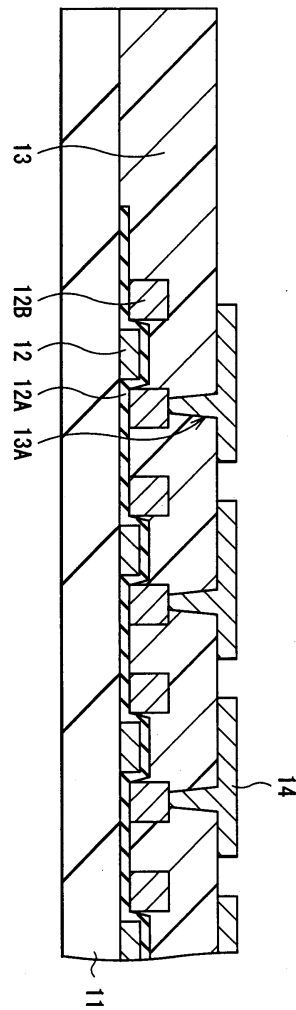
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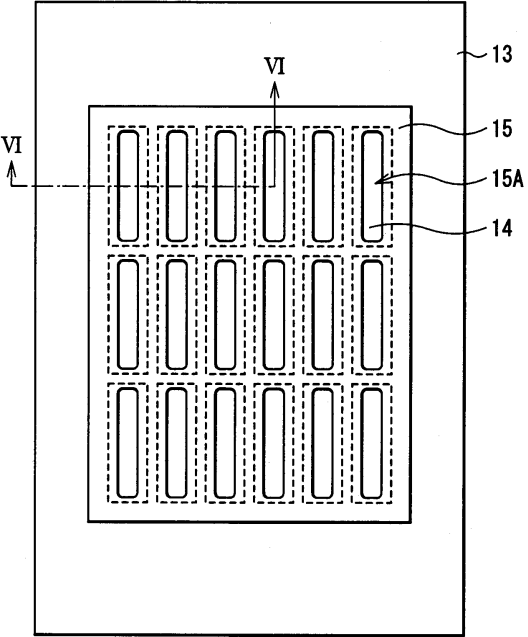
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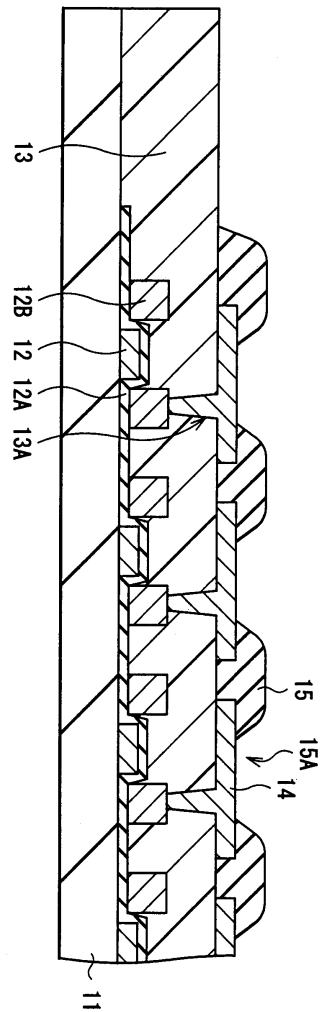
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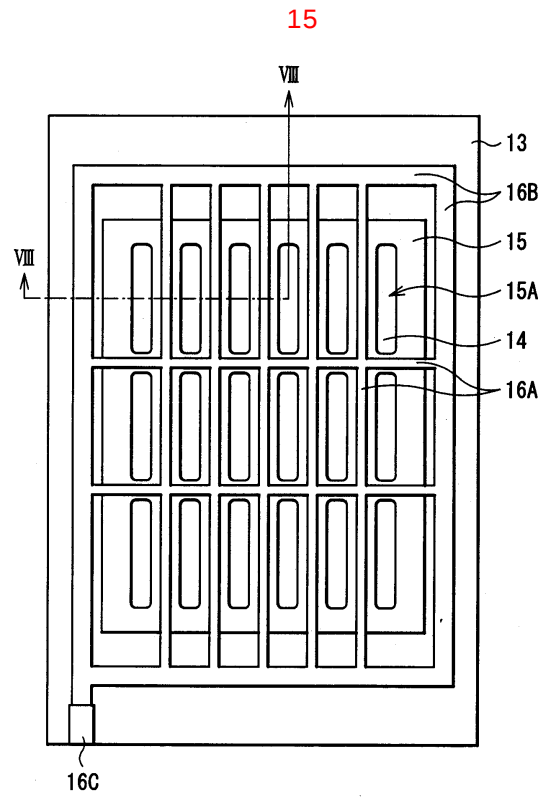


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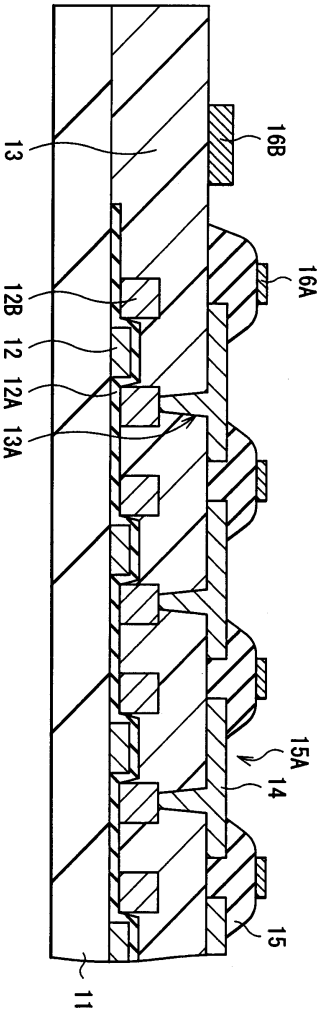


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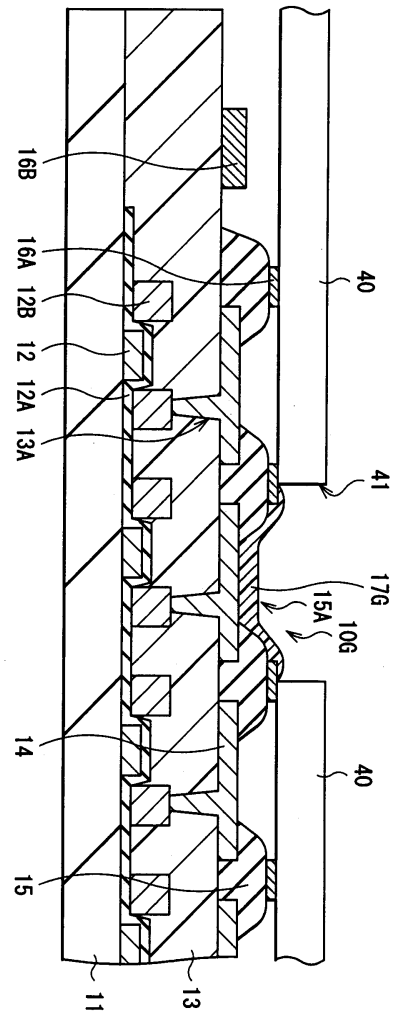




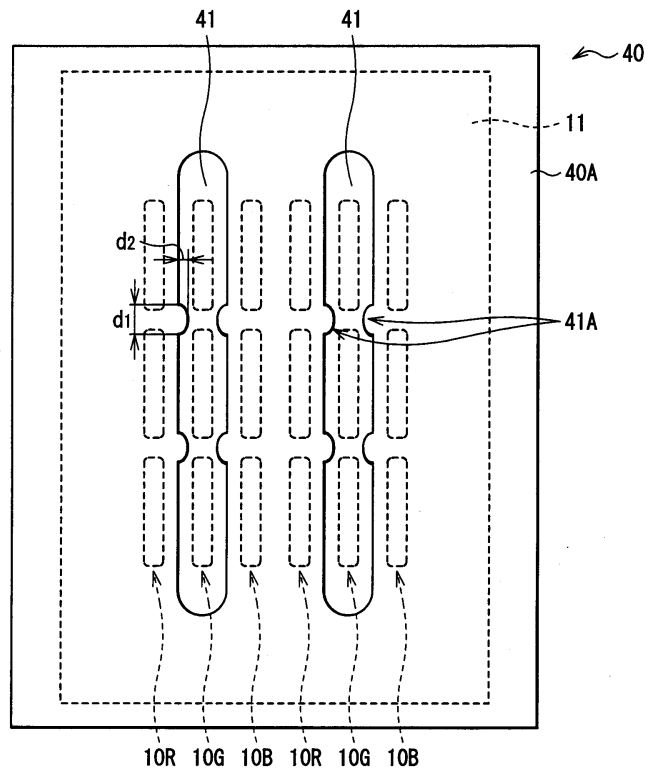
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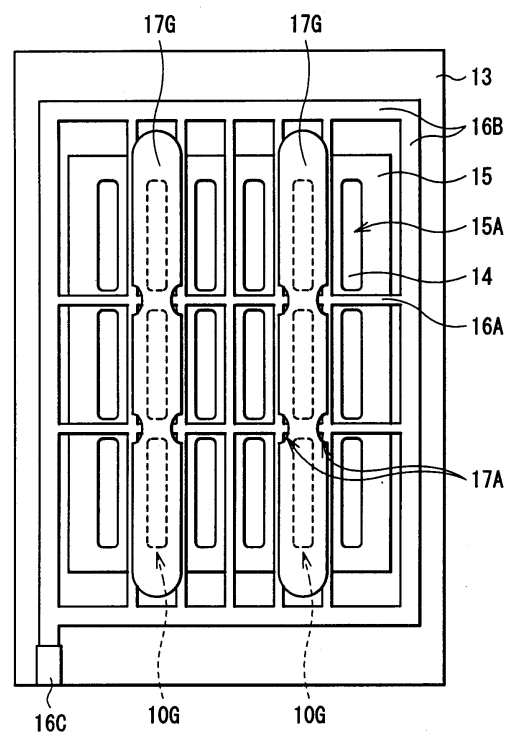
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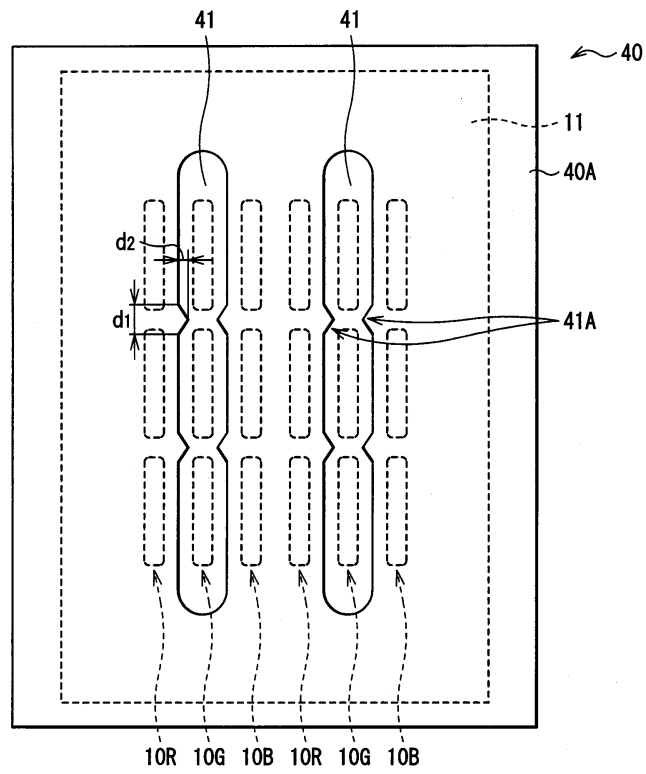
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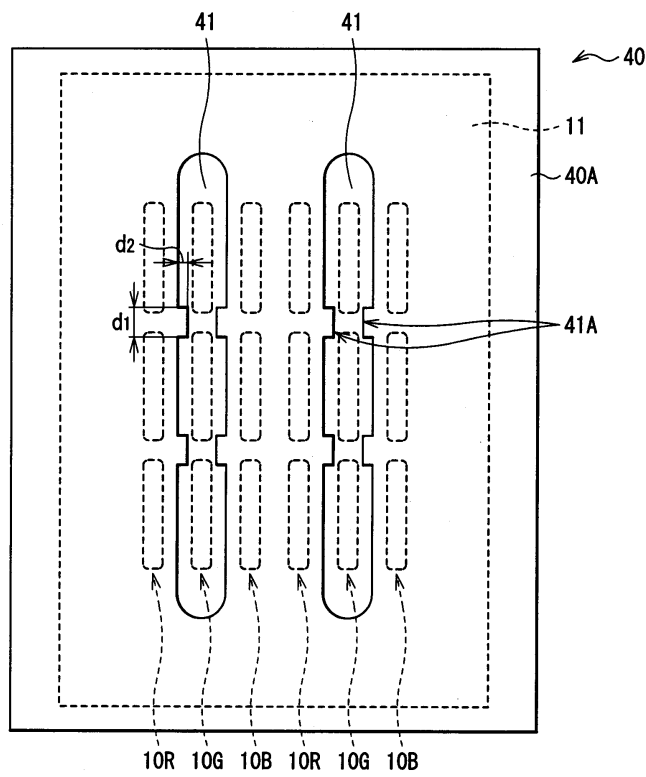
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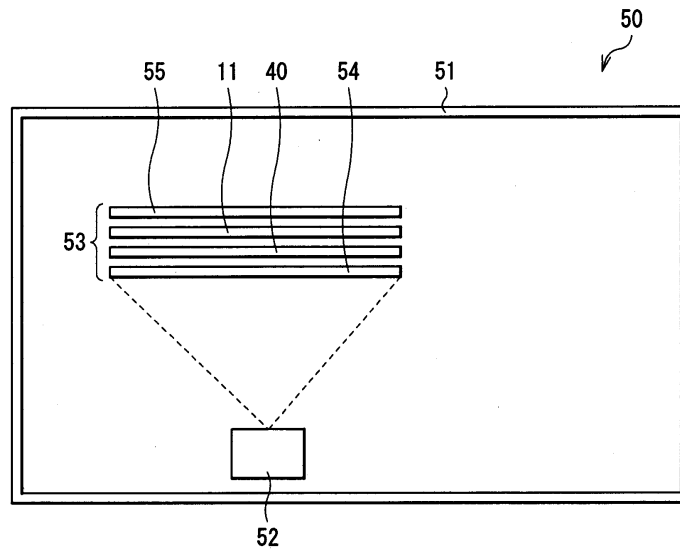
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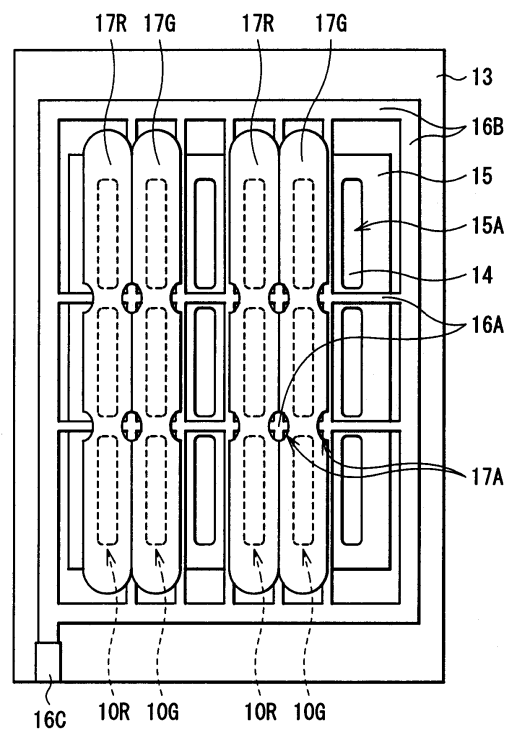
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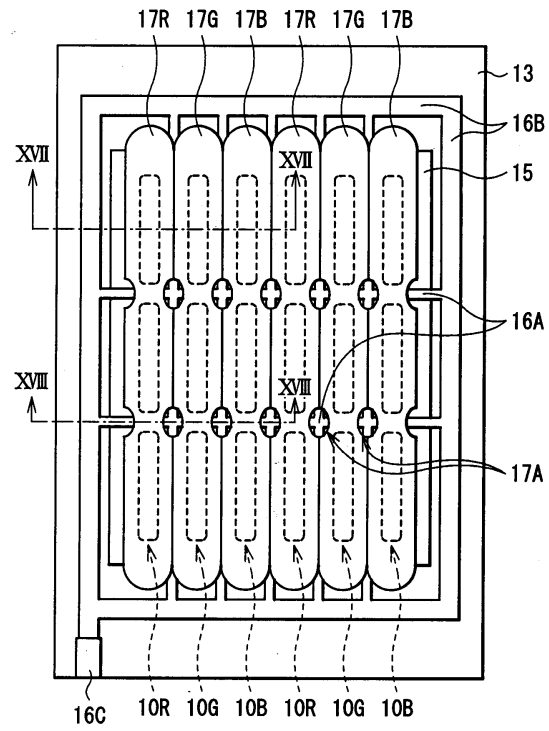
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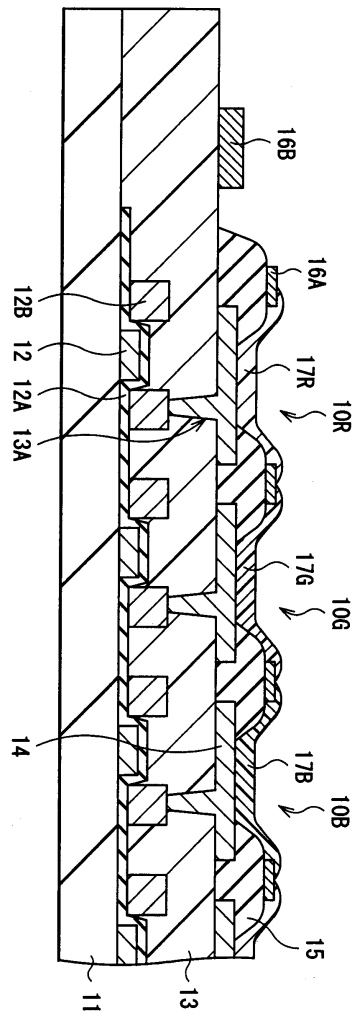
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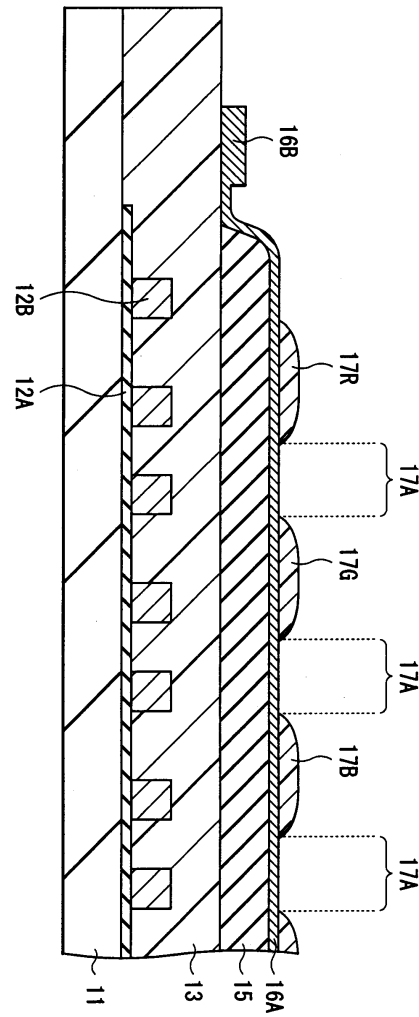
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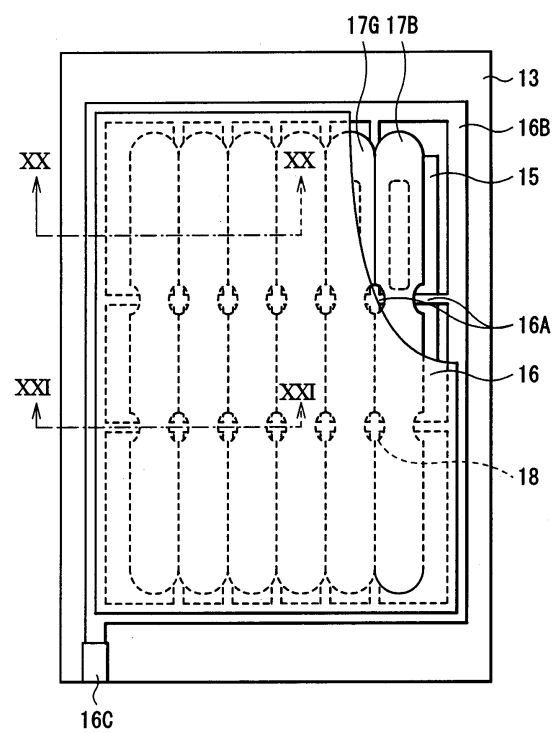
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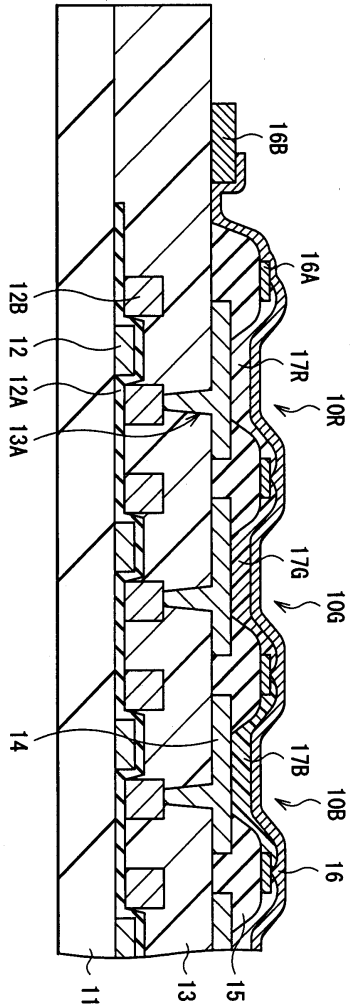


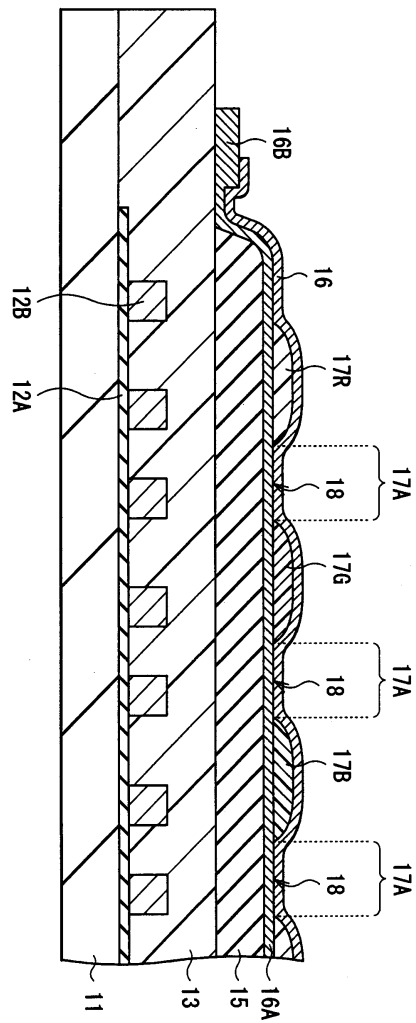
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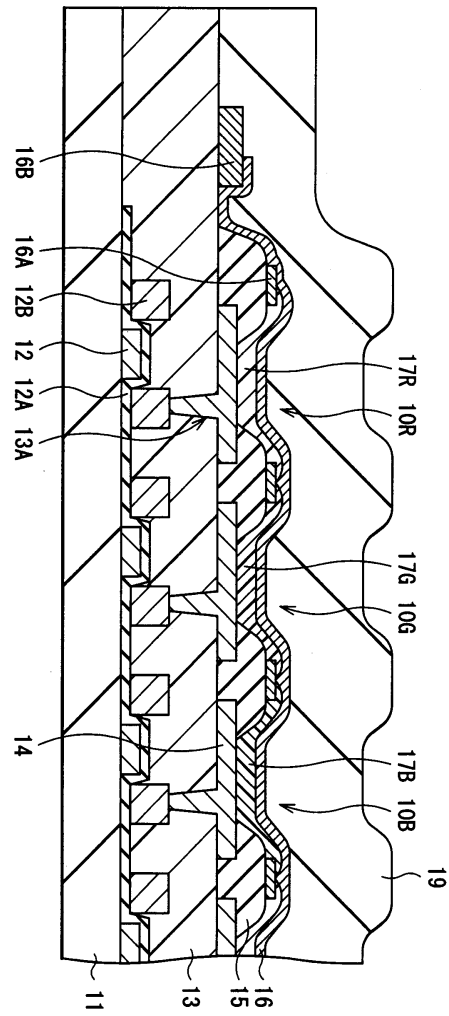
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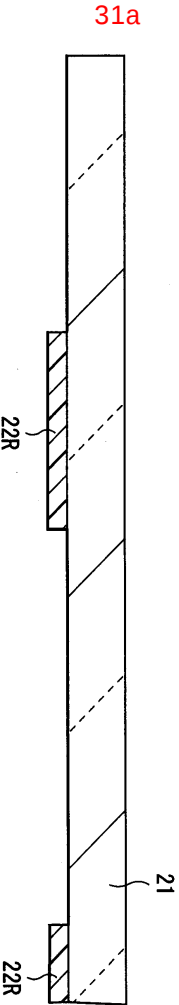


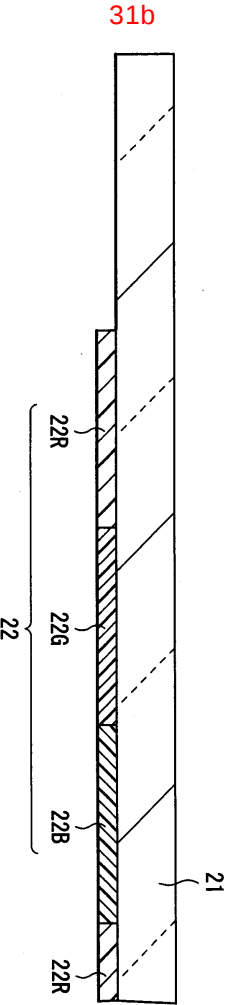




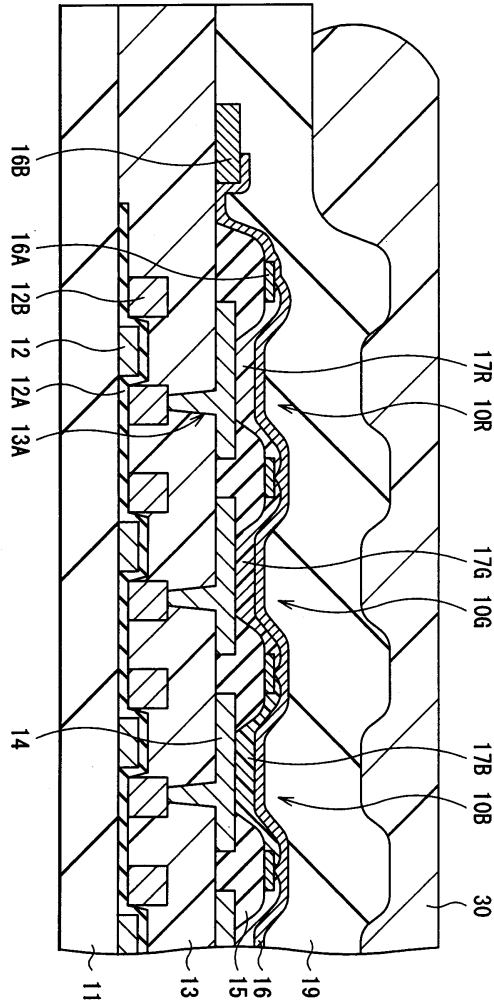
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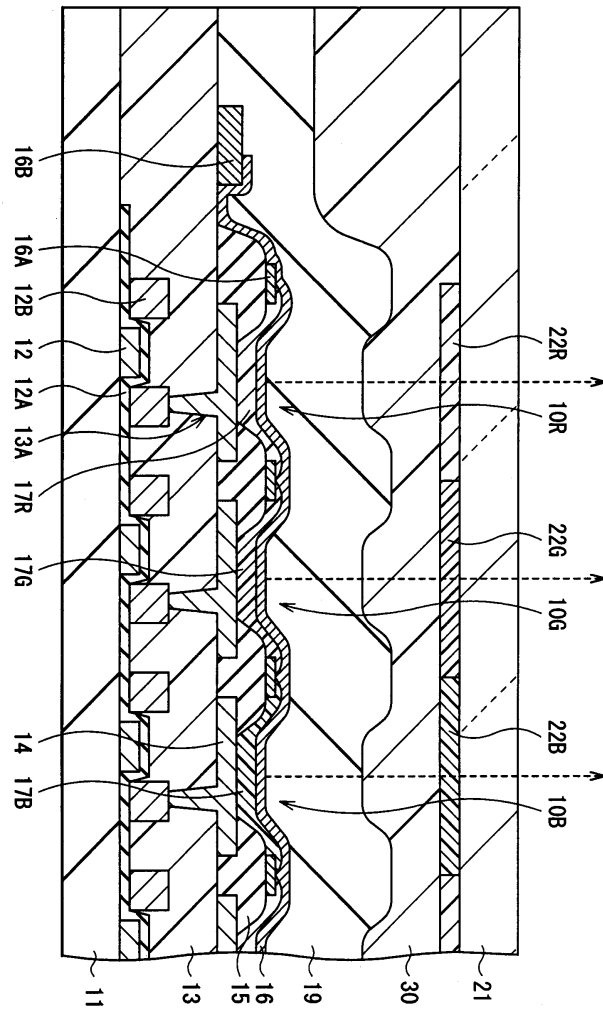




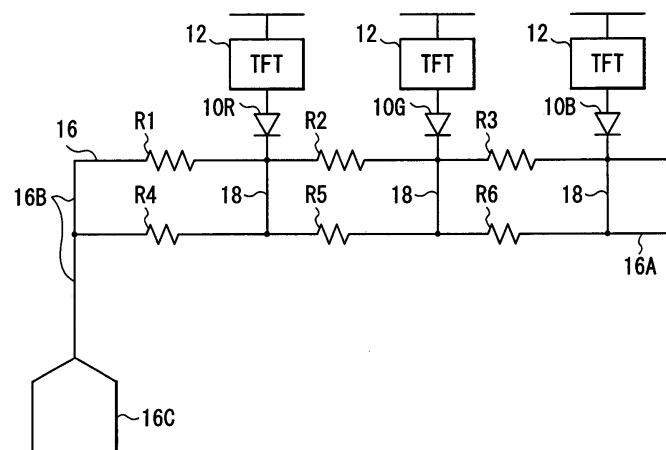
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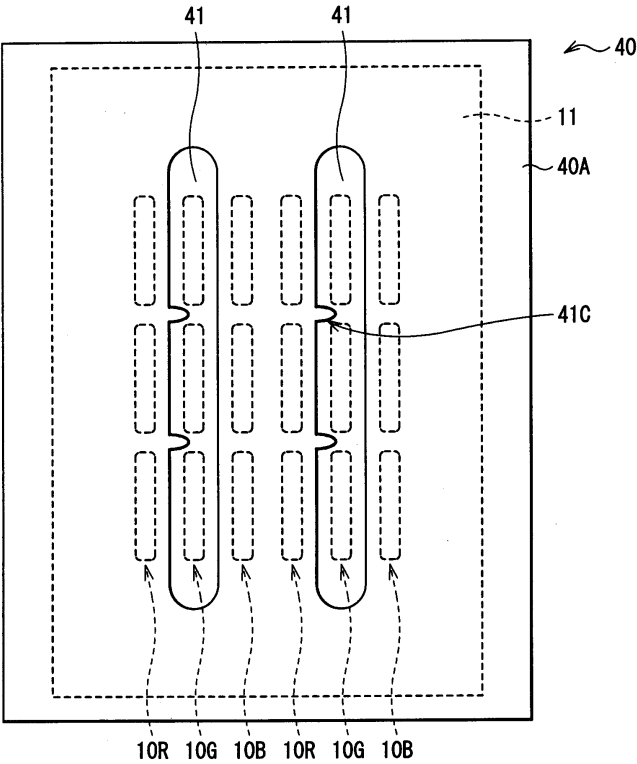
33



34



35



专利名称(译)	沉积掩模，使用沉积掩模制造显示单元的方法，		
公开(公告)号	KR1020040097918A	公开(公告)日	2004-11-18
申请号	KR1020040033019	申请日	2004-05-11
[标]申请(专利权)人(译)	索尼公司		
申请(专利权)人(译)	索尼有限公司		
当前申请(专利权)人(译)	索尼有限公司		
[标]发明人	YAMAGUCHI MASARU		
发明人	YAMAGUCHI,MASARU		
IPC分类号	H01L51/40 H01L51/30 H01L51/50 H01L27/32 H01L51/00 H05B33/10 H05B33/06 H05B33/04 H01L51/52 H01L51/56 C23C14/04		
CPC分类号	H01L51/005 H01L27/3244 H01L2251/5315 H01L27/3211 H01L51/0081 H01L51/0062 H01L51/5203 H01L51/0008 C23C14/042 H01L51/0059 H01L51/56 H01L27/3276 H01L51/0035 H01L51/5221 H01L51/5253 H01L2251/301 H01L2251/303 H01L2251/558 H01L27/32 H01L51/0011 H01L51/0012 H01L51/5012 H01L51/5206 H01L51/5212 H01L51/5228 H01L51/5262 H01L2227/323		
代理人(译)	MOON , KYOUNG金 KIM , HAK SOO		
优先权	2003132791 2003-05-12 JP		
其他公开文献	KR101021542B1		
外部链接	Espacenet		

摘要(译)

用途：提供适合于使用有机发光器件制造显示单元的沉积掩模，使用该沉积掩模的显示单元的制造方法，以及显示单元，以制造能够通过使用改善显示单元的孔径比的沉积掩模沉积掩模。组成：沉积掩模形成显示单元的有机发光器件共有的连续有机层。显示单元具有矩阵结构，并且根据沉积方法在基板（11）上包括多个有机发光器件（10R，10G，10B）的多个线和列。沉积掩模包括主体部分和突起。主体部分包括一个或多个条形开口，用于形成与矩阵结构的至少两条线共用的连续有机层。并且突起设置在主体部分上，以便部分地突出到开口中。

